

Title (en)

SOLAR CELLS WITH A BARRIER LAYER BASED ON POLYSILAZANE

Title (de)

SOLARZELLEN MIT EINER BARRIERESCHICHT AUF BASIS VON POLYSILAZAN

Title (fr)

CELLULES SOLAIRES POURVUES D'UNE COUCHE BARRIÈRE À BASE DE POLYSILAZANE

Publication

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Application

EP 10709428 A 20100316

Priority

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Abstract (en)

[origin: WO2010105798A1] The invention relates to a thin-film solar cell (10) comprising a substrate (1) of metal or glass, a dielectric barrier layer (2) based on polysilazane and a photovoltaic layer structure (4) of the copper-indium sulphide (CIS) type or the copper-indium-gallium selenide (CIGSe) type.

IPC 8 full level

H01L 31/032 (2006.01)

CPC (source: EP US)

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Citation (search report)

See references of WO 2010105798A1

Citation (examination)

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